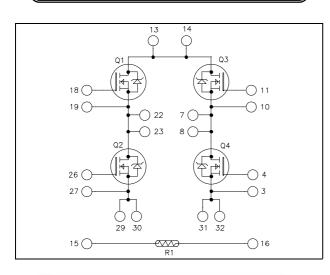


Full - Bridge MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

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$V_{DSS} = 500V$

 $R_{DSon} = 65m\Omega \text{ typ}$ (a) $Tj = 25^{\circ}C$

 $I_D = 51A (a) T_C = 25^{\circ}C$

Application

- Welding converters
 - Switched Mode Power Supplies
 - Uninterruptible Power Supplies

Features

• Power MOS 7[®] FREDFETs

- Low R_{DSon}
- Low input and Miller capacitance
- Low gate charge
- Fast intrinsic reverse diode
- Avalanche energy rated
- Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Voltage		500	V
т	Continuous Drain Current	$T_c = 25^{\circ}C$	51	
ID	I _D Continuous Drain Current	$T_c = 80^{\circ}C$	38	А
I _{DM}	Pulsed Drain current		204	
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		78	mΩ
PD	Power Dissipation $T_c = 25^{\circ}C$		390	W
I _{AR}	Avalanche current (repetitive and non repetitive)		51	А
EAR	Repetitive Avalanche Energy		50	m I
E _{AS}	Single Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APTM50HM65FT3G – Rev 3 December, 2017



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Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			100	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 25.5A$		65	78	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$	3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 V, V_{DS} = 0V$			±150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		7000		
Coss	Output Capacitance	$V_{DS} = 25V$		1400		pF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		90		
Qg	Total gate Charge	$V_{GS} = 10V$		140		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250V$		40		nC
Q_{gd}	Gate – Drain Charge	$I_D = 51A$		70		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		21		
Tr	Rise Time	$V_{GS} = 15V$		38		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 333V$ $I_D = 51A$		75		
$T_{\rm f}$	Fall Time	$R_G = 3\Omega$		93		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		1035		T
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ I _D = 51A, R _G = 3Ω		845		μĴ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$, $V_{Bus} = 333V$ $I_D = 51A$, $R_G = 3\Omega$		1556		Ŧ
E_{off}	Turn-off Switching Energy			1013		μJ
R_{thJC}	Junction to Case Thermal Resistan	ce			0.32	°C/W

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
т	Continuous Source current		$Tc = 25^{\circ}C$			51		
Is	(Body diode)		$Tc = 80^{\circ}C$			38	А	
V _{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -51A$	L			1.3	V	
dv/dt	Peak Diode Recovery 1					15	V/ns	
t _{rr}	Deviance Deservoury Times		$T_j = 25^{\circ}C$			270	na	
	Reverse Recovery Time	$I_{\rm S} = -51A$ $V_{\rm R} = 333V$	$T_j = 125^{\circ}C$			540	ns	
Q _{rr}	Reverse Recovery Charge	$v_{\rm R} = 355 v$ di _s /dt = 100A/µs	$T_j = 25^{\circ}C$		2.6		μC	
	Reverse Recovery Charge	•	$T_j = 125^{\circ}C$		9.6		μΟ	

 $\label{eq:linear} \begin{array}{ll} \bullet \ dv/dt \ numbers \ reflect \ the \ limitations \ of \ the \ circuit \ rather \ than \ the \ device \ itself. \\ I_S \leq \ -51A \quad di/dt \leq \ 700A/\mu s \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ C \end{array}$



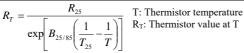
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Thermal and package characteristics

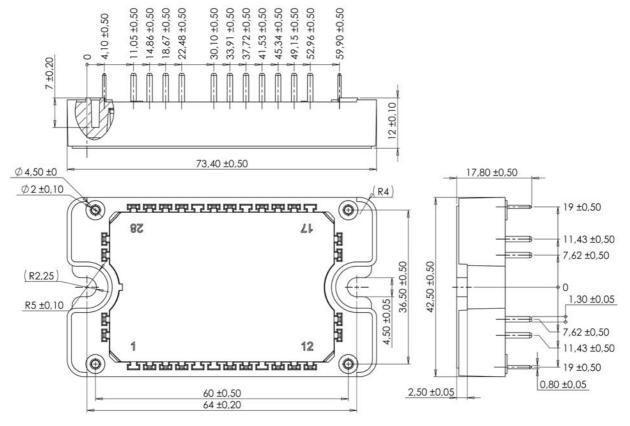
Symbol	Characteristic				Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz					V
TJ	Operating junction temperature range			-40	150	
T _{JOP}	Recommended junction temperature under sy	ons	-40	T _J max - 25	°C	
T _{STG}	Storage Temperature Range			-40	125	C
T _C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic			Тур	Max	Unit
R ₂₅	Resistance @ 25°C	C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		$T_C=100^{\circ}C$		4		%



Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

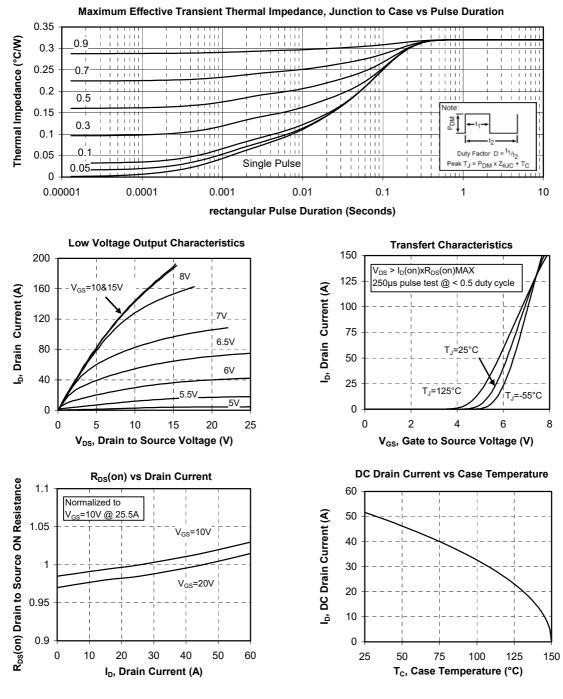
www.microsemi.com

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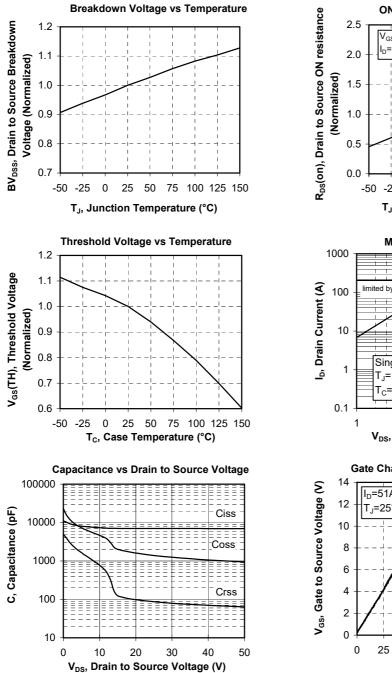
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Typical Performance Curve

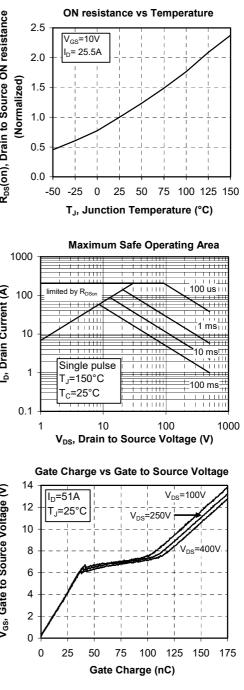




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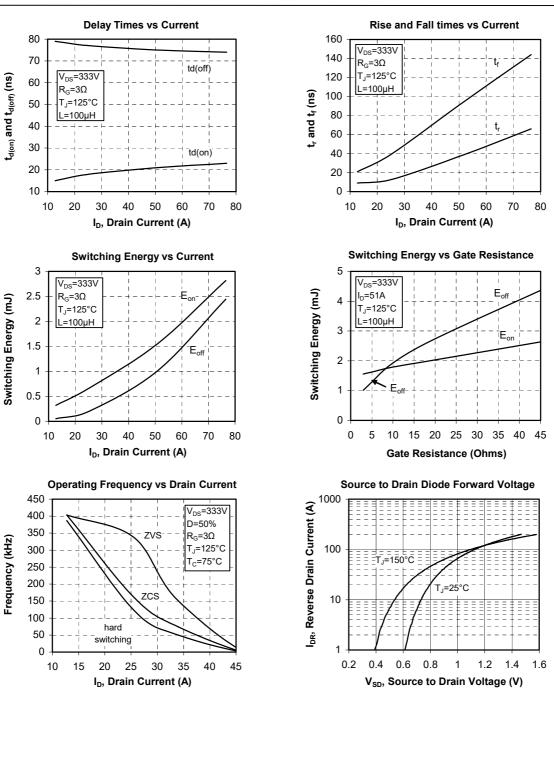
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